# NCE40P70K

## NCE P-Channel Enhancement Mode Power MOSFET

## **Description**

The NCE40P70K uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge .This device is well suited for high current load applications.

#### **General Features**

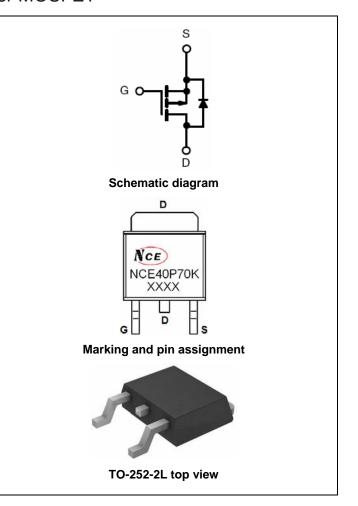
- $V_{DS}$  =-40V, $I_{D}$  =-70A  $R_{DS(ON)}$  <10m $\Omega$  @  $V_{GS}$ =-10V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E<sub>AS</sub>
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

#### **Application**

- Power switch
- Load switch in high current applications
- DC/DC converters

100% UIS TESTED!

100% AVds TESTED!



## **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE40P70K	NCE40P70K	TO-252-2L	-	-	-

## Absolute Maximum Ratings (T<sub>C</sub>=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	-40	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous	I <sub>D</sub>	-70	А
Drain Current-Continuous(T <sub>C</sub> =100℃)	I <sub>D</sub> (100℃)	-35	А
Pulsed Drain Current	I <sub>DM</sub>	-115	А
Maximum Power Dissipation	P <sub>D</sub>	65	W
Derating factor		0.52	W/°C
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	1020	mJ
Operating Junction and Storage Temperature Range	$T_{J}$ , $T_{STG}$	-55 To 150	$^{\circ}$



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# NCE40P70K

## **Thermal Characteristic**

Thermal Resistance, Junction-to-Case(Note 2)	$R_{ heta JC}$	1.92	°C/W	
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## Electrical Characteristics (T<sub>C</sub>=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA -40		-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-40V,V <sub>GS</sub> =0V	=-40V,V <sub>GS</sub> =0V -		-1	μΑ
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)	·					
Gate Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250μA	-1.2	-1.9	-2.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-20A	-	7.5	10	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =-10V,I <sub>D</sub> =-20A	-	50	-	S
Dynamic Characteristics (Note4)	·					
Input Capacitance	C <sub>lss</sub>	\/ 00\/\/ 0\/	-	6460	-	PF
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ =-20V, $V_{GS}$ =0V, F=1.0MHz	-	684	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.UIVID2	-	600	-	PF
Switching Characteristics (Note 4)	<u>.</u>		•			
Turn-on Delay Time	t <sub>d(on)</sub>		-	15	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =-20V, $R_L$ =2 $\Omega$ ,	-	12	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =-10 $V$ , $R_G$ =1 $\Omega$	-	70	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	18	-	nS
Total Gate Charge	Qg	V 00 L 00 A	-	106		nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ =-20, $I_{D}$ =-20A, $V_{GS}$ =-10V	-	22		nC
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =-10V	-	27		nC
Drain-Source Diode Characteristics	<u>.</u>		•			•
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =-10A	-		-1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	-70	Α
Reverse Recovery Time	t <sub>rr</sub>	TJ = 25°C, IF =- 10A	-	53		nS
Reverse Recovery Charge	Qrr	di/dt = -100A/µs(Note3)	-	50		nC
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				y LS+LD)
	-011					

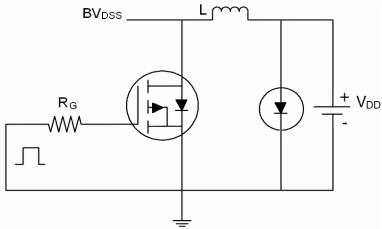
#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.
- 3. Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production
- **5.** E<sub>AS</sub> condition: Tj=25  $^{\circ}\text{C}$  ,V<sub>DD</sub>=-20V,V<sub>G</sub>=-10V,L=1mH,Rg=25 $\Omega$ ,I<sub>AS</sub>=45A

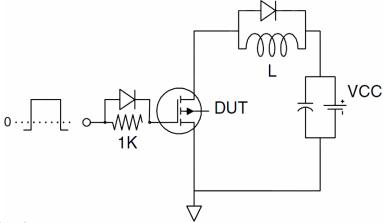


## **Test Circuit**

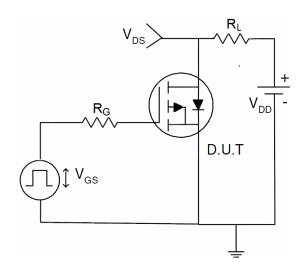
## 1) E<sub>AS</sub> Test Circuit



## 2) Gate Charge Test Circuit

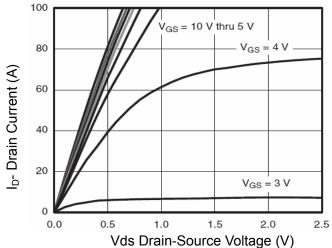


## 3) Switch Time Test Circuit

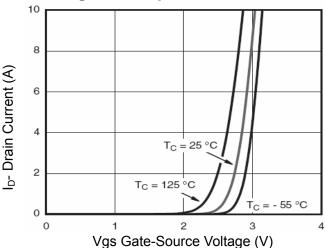




## Typical Electrical and Thermal Characteristics (Curves)



**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

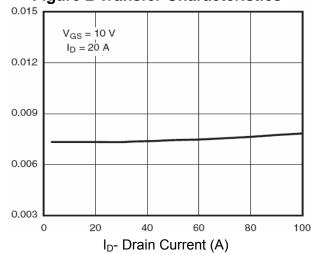
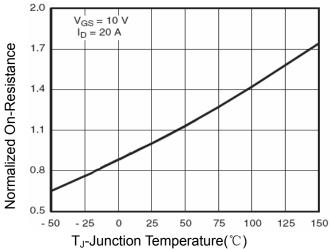


Figure 3 Rdson- Drain Current



**Figure 4 Rdson-Junction Temperature** 

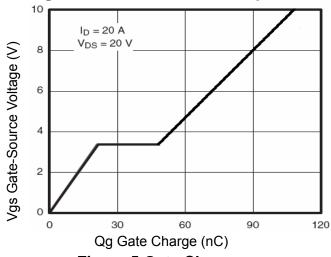


Figure 5 Gate Charge

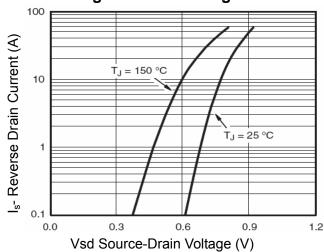


Figure 6 Source- Drain Diode Forward



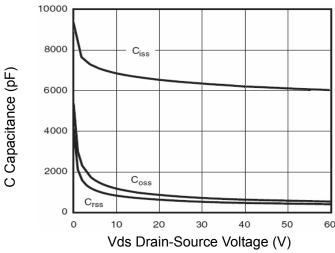


Figure 7 Capacitance vs Vds

1000

(V) tubuno uigu 1

100 R<sub>DS(ON)</sub> 100 uigu 1

100 Log 100 lo

**Figure 8 Safe Operation Area** 

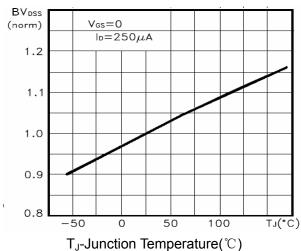


Figure 9 BV<sub>DSS</sub> vs Junction Temperature

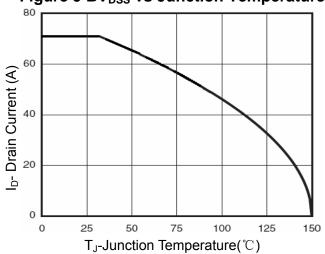


Figure 10 ID Current Derating vs Junction Temperature

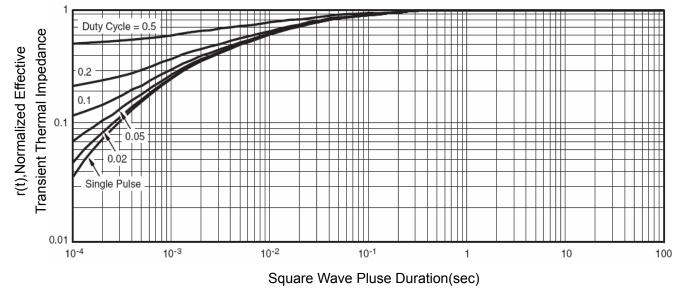
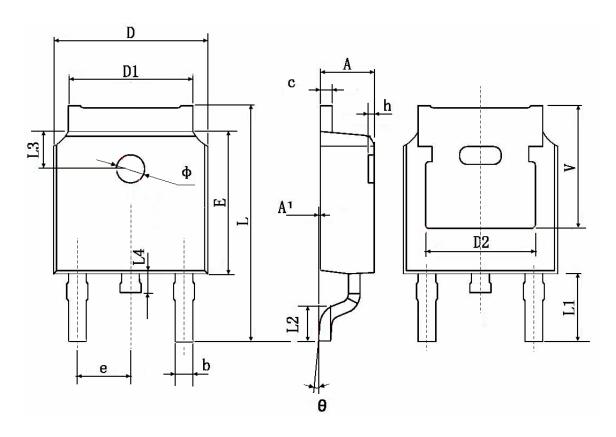


Figure 11 Normalized Maximum Transient Thermal Impedance

**Pb Free Product** 



## **TO-252 Package Information**



Symbol	Dimensions	In Millimeters	Dimensions In Inches			
	Min.	Max.	Min.	Max.		
А	2.200	2.400	0.087	0.094		
A1	0.000	0.127	0.000	0.005		
b	0.660	0.860	0.026	0.034		
С	0.460	0.580	0.018	0.023		
D	6.500	6.700	0.256	0.264		
D1	5.100	5.460	0.201	0.215		
D2	0.483	TYP.	0.190 TYP.			
Е	6.000	6.200	0.236	0.244		
е	2.186	2.386	0.086	0.094		
L	9.800	10.400	0.386	0.409		
L1	2.900 TYP.		0.114 TYP.			
L2	1.400	1.700	0.055	0.067		
L3	1.600	1.600 TYP. 0.063 T		YP.		
L4	0.600	1.000	0.024	0.039		
Ф	1.100	1.300	0.043	0.051		
θ	0°	8°	0°	8°		
h	0.000	0.300	0.000	0.012		
V	5.350	5.350 TYP. 0.211 TYP.				



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